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APPLICATION NO. FILING DATE		FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.		
10/695,748 10/30/2003		Bruce B. Doris	FIS920030264 6189 (00750483AA)			
30743	7590 10/13/2005		EXAMINER			
	1, CURTIS & CHRIST	LE, THAO X				
11491 SUNS SUITE 340	SET HILLS ROAD	ART UNIT	PAPER NUMBER			
RESTON, V	/A 20190	2814				
				DATE MAILED: 10/13/2005		

Please find below and/or attached an Office communication concerning this application or proceeding.

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Office Action Summary		Application	ı No.	Applicant(s)	U"			
		10/695,748	;	DORIS ET AL.				
		Examiner		Art Unit				
		Thao X. Le		2814				
	MAILING DATE of this communication app	pears on the	cover sheet with the c	orrespondence ac	dress			
Period for Rep	ENED STATUTORY PERIOD FOR REPLY	V IS SET TO	SEXPIRE 2 MONTH(S) FROM				
THE MAILI - Extensions of after SIX (6) - If the period if NO period i	NG DATE OF THIS COMMUNICATION. If time may be available under the provisions of 37 CFR 1.13 MONTHS from the mailing date of this communication. for reply specified above is less than thirty (30) days, a reply for reply is specified above, the maximum statutory period w ply within the set or extended period for reply will, by statute, the served by the Office later than three months after the mailing at term adjustment. See 37 CFR 1.704(b).	36(a). In no ever y within the statut will apply and will g, cause the applic	it, however, may a reply be tim ory minimum of thirty (30) days expire SIX (6) MONTHS from a ation to become ABANDONEI	ely filed s will be considered time the mailing date of this co (35 U.S.C. § 133).	ly. ommunication.			
Status								
1)⊠ Resp	oonsive to communication(s) filed on 23 M	1ay 2005.						
2a)⊠ This	action is FINAL . 2b)⊠ This	action is no	n-final.					
3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits								
close	ed in accordance with the practice under E	Ex parte Qua	yle, 1935 C.D. 11, 45	3 O.G. 213.	;			
Disposition of	Claims							
4) Clain	4) Claim(s) <u>1-19</u> is/are pending in the application.							
	4a) Of the above claim(s) <u>1-9</u> is/are withdrawn from consideration.							
5) Clain	☐ Claim(s) is/are allowed. ☐ Claim(s) 10-12,16-19 is/are rejected.							
6)⊠ Clain								
7) Clain	Claim(s) <u>13-15</u> is/are objected to.							
8) Clain	Claim(s) are subject to restriction and/or election requirement.							
Application Pa	apers			•				
9)⊠ The s	specification is objected to by the Examine	er.						
10)⊠ The c	Irawing(s) filed on <u>02 September 2005</u> is/a	are: a)⊠ ac	cepted or b) object	ted to by the Exa	miner.			
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).								
	Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).							
11)∏ The c	oath or declaration is objected to by the Ex	xaminer. Not	e the attached Office	Action or form P	TO-152.			
Priority under	35 U.S.C. § 119							
12)∏ Ackno a)∏ All 1.∏	owledgment is made of a claim for foreign b) ☐ Some * c) ☐ None of: Certified copies of the priority documents			-(d) or (f).				
2.□	Certified copies of the priority documents			on No				
3.					l Stage			
	application from the International Bureau							
* See the attached detailed Office action for a list of the certified copies not received.								
Attachment(s)			_					
	eferences Cited (PTO-892)		4) Interview Summary Paper No(s)/Mail Da					
	raftsperson's Patent Drawing Review (PTO-948) Disclosure Statement(s) (PTO-1449 or PTO/SB/08))		ate Patent Application (PT	O-152)			
· —)/Mail Date	·	6) Other:					

DETAILED ACTION

Election/Restrictions

1. Applicant's election with traverse of claims 10-19 dated 02 Sept. 2005 is acknowledged. The traversal is on the ground that 'the Examiner has not provided a prime facie demonstration of distinctness between the identified invention'. This is found not persuasive because the alternate method proposed by the Examiner would be distinct from the claimed process. In Addition, Applicant has not provided a convincing argument that the materially different processes would not be suitable in producing the recited device. Finally, the search is not coexisting as evidenced by the different fields of search for the process and the product as cited in the restriction along with Office Action dated 06/02/05.

This requirement is deemed still proper and is therefore made FINAL.

2. This application contains claims 1-9 drawn to an invention nonelected with traverse dated02 Sept. 2005. A complete reply to the final rejection must include cancellation of nonelected claims or other appropriate action (37 CFR 1.144) See MPEP § 821.01.

Specification

3. The disclosure is objected to because of the following informalities: page 10 line 28, spacer 11.

Drawings

4. The drawings were received on 02 Sept. 2005. These drawings are acceptable.

Claim Rejections - 35 USC § 112

- 5. The following is a quotation of the second paragraph of 35 U.S.C. 112:
 - The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.
- 6. Claims 13-19 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention. Recited the limitation "the nMOS" and 'the pMOS' in claims 13, 15, 17-19. There is insufficient antecedent basis for this limitation in the claim.

Assuming 'the nMOS' and 'the pMOS' are 'the first' and 'the second' transistors, respectively.

Claim Rejections - 35 USC § 102

7. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

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8. Claims 10-12 and 16-19 are rejected under 35 U.S.C. 102(e) as being anticipated by US Pub2003/0181005 to Hachimine et al.

Regarding claim 10, Hachimine discloses a structure that adjusts carrier mobility in CMOS transistors in fig. 15 comprising: a substrate 1 [0164], a first transistor (n-ch MISFET) having a gate dielectric 5, gate electrode 6, and source/drain 7/10 [0165], and gate region 12 [0167], formed on said substrate 1, a second transistor (p-ch MISFET) having a gate dielectric 5, gate electrode 6, and source/drain 8/11, and gate regions 12, fig. 15, formed on said substrate 1, a first film 14a providing tensile stress [0168] at least at the channel of first transistor, a second film 14b providing compressive stress [0168] at least at the channel of second transistor, a portion of said second film 14b extending in the same region of said substrate as a portion of said first film 14a, fig. 15, and a shear force isolation layer 15 [0170] separating said first film 14a and said second film 14b and said tensile and compressive stress therein in at least one area, fig. 15.

Regarding claim 11, Hachimine discloses the structure as recited in claim 10 wherein the first and second films can be composed of nitride, oxide, or other material that exhibits either tensile or compressive properties [0168].

Regarding claim 12, Hachimine discloses the structure as recited in claim 11 wherein the first and second stressed films 14a/14b are separated by said shear force isolation layer 15 at all points of overlap, fig. 15.

Regarding claim 16, Hachimine discloses the structure as recited in claim 11 wherein the first and second stressed films 14a/14b are separated by a shear force isolation layer 5 at selected areas.

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Regarding claim 17, Hachimine discloses the structure as recited in claim 16 wherein the first stressed film 14a, closer to the substrate than the second stressed film 14b, fully surrounds the NMOS transistor, fig. 31.

Regarding claim 18, Hachimine discloses th structure as recited in claim 17 wherein said first stressed film 14a is the only separation between the nMOS transistor and said second stressed film 14b, fig. 1.

Regarding claim 19, Hachimine discloses the structure as recited in claim 17 wherein said second stressed film 14b surrounds the oxide liner 15 at the sides of the PMOS transistor gate electrode 6 with the top of the gate directly engaged with said second stressed film 14b, fig. 31.

Allowable Subject Matter

9. Claims 13-15 would be allowable if rewritten to overcome the rejection(s) under 35 U.S.C. 112, 2nd paragraph, set forth in this Office action and to include all of the limitations of the base claim and any intervening claims. The prior art of record neither anticipated nor rendered obvious all the limitations of claim 13 including 'the first stressed film, closer to the substrate than the second stressed film, does not fully surround the nMOS transistor, but rather the sides only, while the remaining surfaces of the nMOS transistor are contacted by said shear force isolation layer'.

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Conclusion

10. Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

11. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Thao X. Le whose telephone number is (571) 272-1708. The examiner can normally be reached on M-F from 8:00 AM - 4:30 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Wael M. Fahmy can be reached on (571) 272 -1705. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

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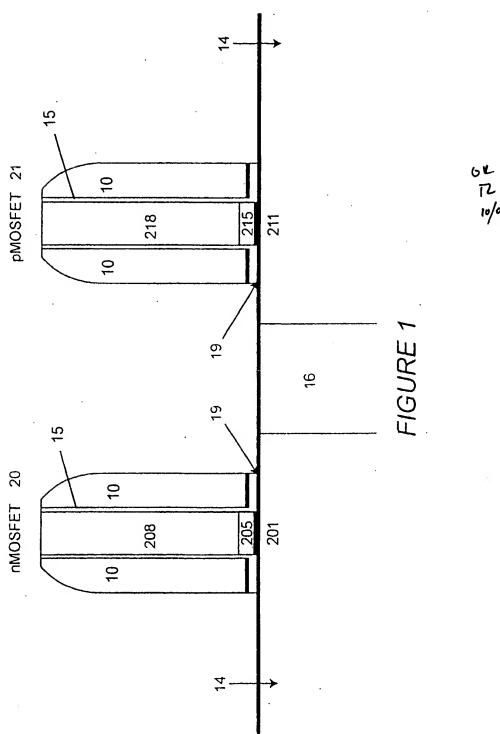
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Thao X. Le Patent Examiner 03 Oct. 2005

LONG PHAM

Replacement Sheet

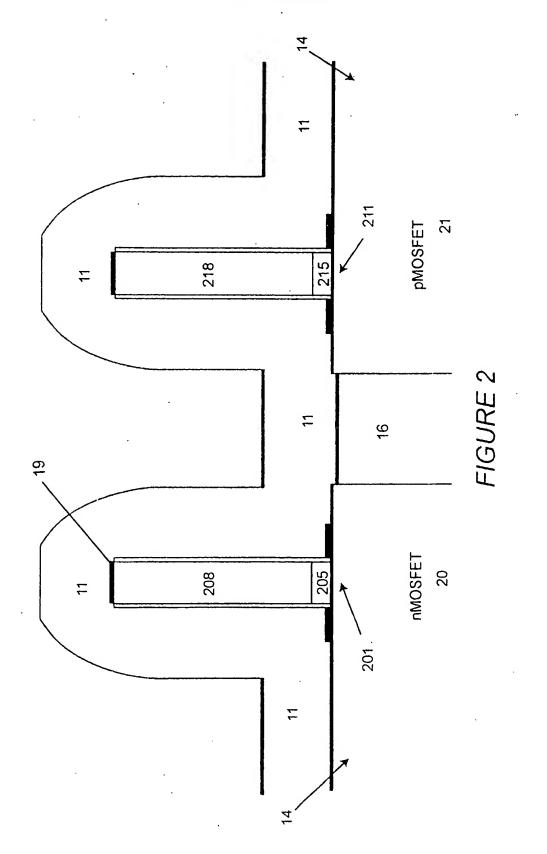
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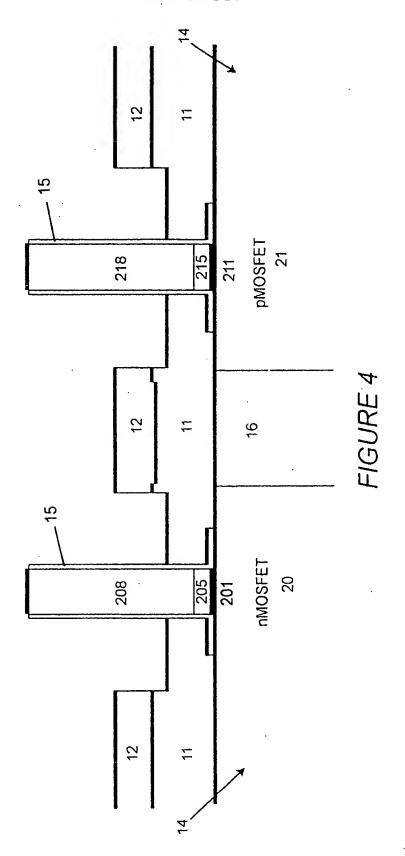
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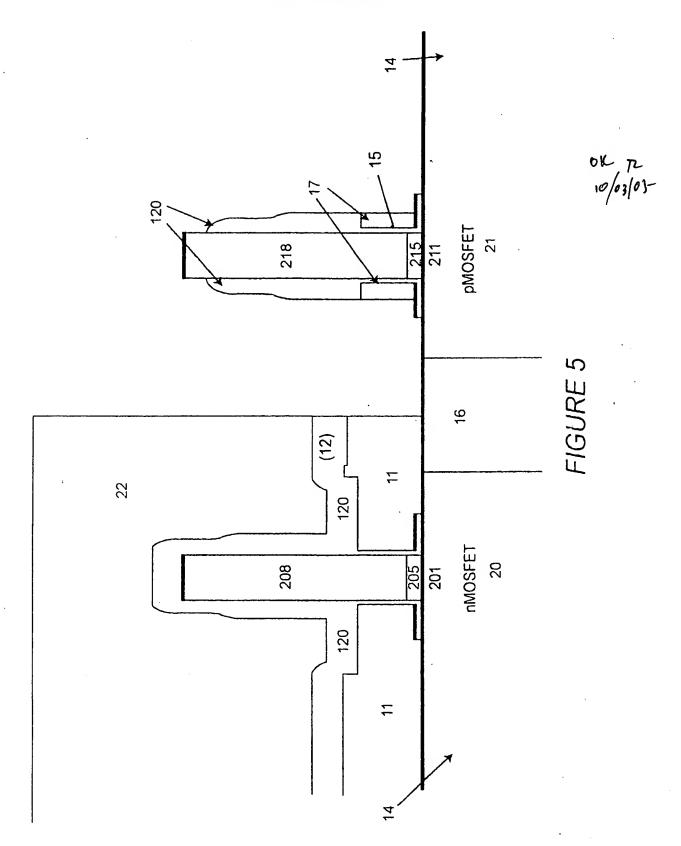
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